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"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "<u>Embedded -</u> <u>Microcontrollers</u>"

Details

Product Status	Active
Core Processor	ARM® Cortex®-M3
Core Size	32-Bit Single-Core
Speed	24MHz
Connectivity	I ² C, IrDA, LINbus, SPI, UART/USART
Peripherals	DMA, PDR, POR, PVD, PWM, Temp Sensor, WDT
Number of I/O	51
Program Memory Size	64KB (64K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	8K x 8
Voltage - Supply (Vcc/Vdd)	2V ~ 3.6V
Data Converters	A/D 16x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	64-TFBGA
Supplier Device Package	64-TFBGA (5x5)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32f100r8h7b

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

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2.1 Device overview

The description below gives an overview of the complete range of peripherals proposed in this family.

Figure 1 shows the general block diagram of the device family.

r											
Peri	pheral	STM32F100Cx				STM32F100Rx				STM32F100Vx	
Flash - Kbytes	16	32	64	128	16	32	64	128	64	128	
SRAM - Kbytes		4	4	8	8	4	4	8	8	8	8
Timoro	Advanced-control		1		1		1		1		1
Timers	General-purpose	5	(1)	(6	5([1)	(6		6
	SPI	1	(2)	:	2	1 ⁽	(2)	:	2		2
Communication interfaces	l ² C	1	(3)	:	2	1((3)	:	2		2
	USART	2 ⁽⁴⁾		;	3		2 ⁽⁴⁾		3		3
	CEC				1						
12-bit synchroniz	zed ADC	1				1				1	
number of chanr	nels	10 channels				16 channels				16 channels	
GPIOs			3	57			5	51			80
12-bit DAC							2				
Number of chann	nels	2									
CPU frequency		24 MHz									
Operating voltag	le	2.0 to 3.6 V									
Operating tempe	Ambient operating temperature: -40 to +85 °C /-40 to +105 °C (see <i>Table</i> Junction temperature: -40 to +125 °C (see <i>Table 8</i>)						ee <i>Table 8</i>)				
Packages			LQF	P48		LQ	FP64,	TFBGA	\64	LQ	FP100

1. TIM4 not present.

2. SPI2 is not present.

3. I2C2 is not present.

4. USART3 is not present.



2.2.23 DAC (digital-to-analog converter)

The two 12-bit buffered DAC channels can be used to convert two digital signals into two analog voltage signal outputs. The chosen design structure is composed of integrated resistor strings and an amplifier in noninverting configuration.

This dual digital Interface supports the following features:

- two DAC converters: one for each output channel
- up to 10-bit output
- left or right data alignment in 12-bit mode
- synchronized update capability
- noise-wave generation
- triangular-wave generation
- dual DAC channels' independent or simultaneous conversions
- DMA capability for each channel
- external triggers for conversion
- input voltage reference V_{REF+}

Eight DAC trigger inputs are used in the STM32F100xx. The DAC channels are triggered through the timer update outputs that are also connected to different DMA channels.

2.2.24 Temperature sensor

The temperature sensor has to generate a voltage that varies linearly with temperature. The conversion range is between 2 V < V_{DDA} < 3.6 V. The temperature sensor is internally connected to the ADC1_IN16 input channel which is used to convert the sensor output voltage into a digital value.

2.2.25 Serial wire JTAG debug port (SWJ-DP)

The ARM SWJ-DP Interface is embedded, and is a combined JTAG and serial wire debug port that enables either a serial wire debug or a JTAG probe to be connected to the target. The JTAG TMS and TCK pins are shared respectively with SWDIO and SWCLK and a specific sequence on the TMS pin is used to switch between JTAG-DP and SW-DP.



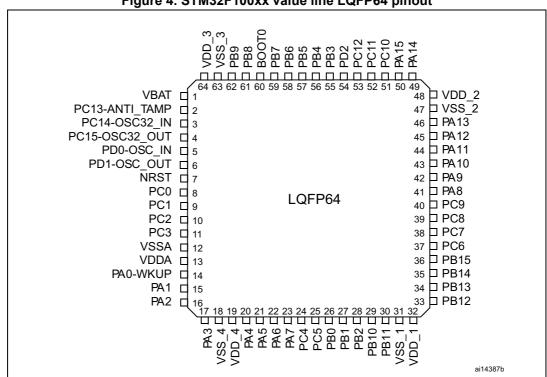
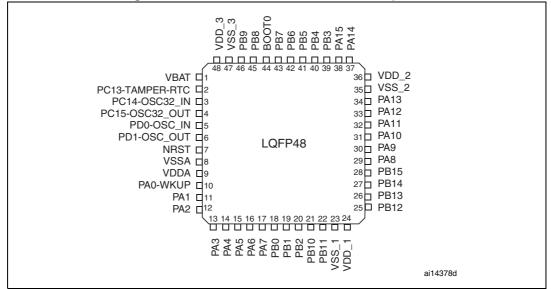


Figure 4. STM32F100xx value line LQFP64 pinout

Figure 5. STM32F100xx value line LQFP48 pinout





DocID16455 Rev 9

	Pi	ns					-	Alternate function	,
LQFP100	LQFP64	TFBGA64	LQFP48	Pin name	Type ⁽¹⁾	I / O level ⁽²⁾	Main function ⁽³⁾ (after reset)	Default	Remap
33	24	H5	-	PC4	I/O	-	PC4	ADC1_IN14	-
34	25	H6	-	PC5	I/O	-	PC5	ADC1_IN15	-
35	26	F5	18	PB0	I/O	-	PB0	ADC1_IN8/TIM3_CH3 ⁽¹²⁾	TIM1_CH2N
36	27	G5	19	PB1	I/O	-	PB1	ADC1_IN9/TIM3_CH4 ⁽¹²⁾	TIM1_CH3N
37	28	G6	20	PB2	I/O	FT	PB2/BOOT1	-	-
38	-	-	-	PE7	I/O	FT	PE7	-	TIM1_ETR
39	-	-	-	PE8	I/O	FT	PE8	-	TIM1_CH1N
40	-	-	-	PE9	I/O	FT	PE9	-	TIM1_CH1
41	-	-	-	PE10	I/O	FT	PE10	-	TIM1_CH2N
42	-	-	-	PE11	I/O	FT	PE11	-	TIM1_CH2
43	-	-	-	PE12	I/O	FT	PE12	-	TIM1_CH3N
44	-	-	-	PE13	I/O	FT	PE13	-	TIM1_CH3
45	-	-	-	PE14	I/O	FT	PE14	-	TIM1_CH4
46	-	-	-	PE15	I/O	FT	PE15	-	TIM1_BKIN
47	29	G7	21	PB10	I/O	FT	PB10	I2C2_SCL ⁽⁹⁾ /USART3_TX (12)	TIM2_CH3 / HDMI_CEC
48	30	H7	22	PB11	I/O	FT	PB11	I2C2_SDA ⁽⁹⁾ /USART3_RX ⁽ 12)	TIM2_CH4
49	31	D6	23	V _{SS_1}	S	-	V _{SS_1}	-	-
50	32	E6	24	V _{DD_1}	S	-	V _{DD_1}	-	-
51	33	H8	25	PB12	I/O	FT	PB12	SPI2_NSS ⁽¹⁰⁾ / I2C2_SMBA ⁽⁹⁾ / TIM1_BKIN ⁽¹²⁾ /USART3_C K ⁽¹²⁾	-
52	34	G8	26	PB13	I/O	FT	PB13	SPI2_SCK ⁽¹⁰⁾ /TIM1_CH1N ⁽¹²⁾ USART3_CTS ⁽¹²⁾	-
53	35	F8	27	PB14	I/O	FT	PB14	SPI2_MISO ⁽¹⁰⁾ / TIM1_CH2N ⁽¹²⁾ / USART3_RTS ⁽¹²⁾	TIM15_CH1
54	36	F7	28	PB15	I/O	FT	PB15	SPI2_MOSI ⁽¹⁰⁾ / TIM1_CH3N / TIM15_CH1N ⁽¹²⁾	TIM15_CH2
55	-	-	-	PD8	I/O	FT	PD8	-	USART3_TX
56	-	-	-	PD9	I/O	FT	PD9	-	USART3_RX

Table 4. Low & medium-density \$	STM32F100xx pin	definitions (continued)



Symbol	Ratings	Max.	Unit				
I _{VDD}	Total current into V_{DD}/V_{DDA} power lines (source) ⁽¹⁾	150					
I _{VSS}	Total current out of V_{SS} ground lines (sink) ⁽¹⁾	150					
I _{IO}	Output current sunk by any I/O and control pin	25					
	Output current source by any I/Os and control pin	-25	mA				
(2)	Injected current on five volt tolerant pins ⁽³⁾	-5 / +0					
I _{INJ(PIN)} ⁽²⁾	Injected current on any other pin ⁽⁴⁾	± 5					
$\Sigma I_{INJ(PIN)}$	Total injected current (sum of all I/O and control pins) ⁽⁵⁾	± 25					

Table 6. Current characteristics

1. All main power (V_{DD} , V_{DDA}) and ground (V_{SS} , V_{SSA}) pins must always be connected to the external power supply, in the permitted range.

2. Negative injection disturbs the analog performance of the device. SeeNote: on page 70.

 Positive injection is not possible on these I/Os. A negative injection is induced by V_{IN}<V_{SS}. I_{INJ(PIN)} must never be exceeded. Refer to *Table 5: Voltage characteristics* for the maximum allowed input voltage values.

 A positive injection is induced by V_{IN}>V_{DD} while a negative injection is induced by V_{IN}<V_{SS}. I_{INJ(PIN)} must never be exceeded. Refer to *Table 5: Voltage characteristics* for the maximum allowed input voltage values.

5. When several inputs are submitted to a current injection, the maximum $\Sigma I_{INJ(PIN)}$ is the absolute sum of the positive and negative injected currents (instantaneous values).

Symbol	Ratings	Value	Unit
T _{STG}	Storage temperature range	–65 to +150	°C
TJ	Maximum junction temperature	150	°C

5.3 Operating conditions

5.3.1 General operating conditions

Table 8. General operating conditions

Symbol	Parameter	Conditions	Min	Max	Unit
f _{HCLK}	Internal AHB clock frequency	-	0	24	
f _{PCLK1}	Internal APB1 clock frequency	-	0	24	MHz
f _{PCLK2}	Internal APB2 clock frequency	-	0	24	
V _{DD}	Standard operating voltage	-	2	3.6	V
V _{DDA} ⁽¹⁾	Analog operating voltage (ADC not used)	tage Must be the same potential		3.6	V
V DDA` '	Analog operating voltage (ADC used)	as V _{DD}		V	
V _{BAT}	Backup operating voltage	-	1.8	3.6	V



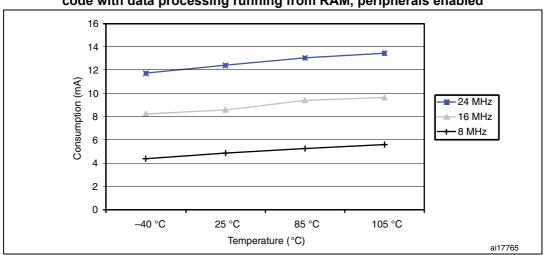


Figure 12. Maximum current consumption in Run mode versus frequency (at 3.6 V) - code with data processing running from RAM, peripherals enabled

Figure 13. Maximum current consumption in Run mode versus frequency (at 3.6 V) - code with data processing running from RAM, peripherals disabled

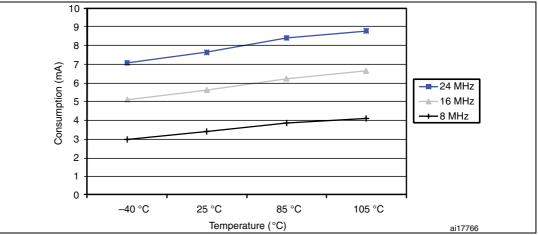


Table 14. Maximum current consumption in Sleep mode, code running from Flash or RAM

Symbol	Parameter	Conditions	£	Ма	Unit	
	Farameter		f _{HCLK}	T _A = 85 °C	T _A = 105 °C	Unit
			24 MHz	9.6	10	
	I _{DD} Supply current in Sleep mode	External clock ⁽²⁾ all peripherals enabled	16 MHz	7.1	7.5	
			8 MHz	4.5	4.8	m 4
DD		External clock ⁽²⁾ , all peripherals disabled	24 MHz	3.8	4	mA
			16 MHz	3.3	3.5	
		F F	8 MHz	2.7	3	

1. Guaranteed by characterization, tested in production at V_{DD} max and f_{HCLK} max with peripherals enabled.

2. External clock is 8 MHz and PLL is on when f_{HCLK} > 8 MHz.



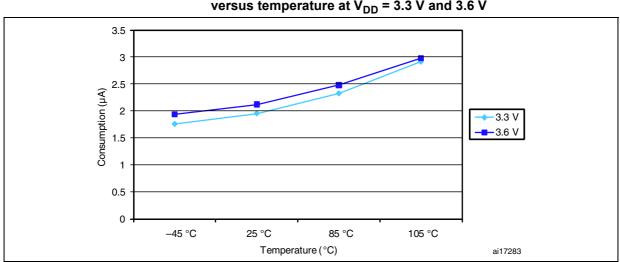


Figure 17. Typical current consumption in Standby mode versus temperature at V_{DD} = 3.3 V and 3.6 V

Typical current consumption

The MCU is placed under the following conditions:

- All I/O pins are in input mode with a static value at V_{DD} or V_{SS} (no load)
- All peripherals are disabled except if it is explicitly mentioned
- When the peripherals are enabled $f_{PCLK1} = f_{HCLK}/4$, $f_{PCLK2} = f_{HCLK}/2$, $f_{ADCCLK} = f_{PCLK2}/4$

The parameters given in *Table 16* are derived from tests performed under the ambient temperature and V_{DD} supply voltage conditions summarized in *Table 8*.



		Conditions		Typical		
Symbol	Parameter		f _{HCLK}	All peripherals enabled ⁽²⁾	All peripherals disabled	Unit
			24 MHz	12.8	9.3	
			16 MHz	9.3	6.6	
			8 MHz	5.1	3.9	
		Running on high-speed external clock with an	4 MHz	3.2	2.5	
	Supply current in Run mode	external clock with an 8 MHz crystal ⁽³⁾	2 MHz	2.1	1.75	- mA
			1 MHz	1.55	1.4	
			500 kHz	1.3	1.2	
			125 kHz	1.1	1.05	
I _{DD}		Running on high-speed	24 MHz	12.2	8.6	
			16 MHz	8.5	6	
			8 MHz	4.6	3.3	
			4 MHz	2.6	1.9	
		internal RC (HSI)	2 MHz	1.5	1.15	
			1 MHz	0.9	0.8	
			500 kHz	0.65	0.6	
			125 kHz	0.45	0.43	

Table 16. Typical current consumption in Run mode, code with data processingrunning from Flash

1. Typical values are measures at $T_A = 25$ °C, $V_{DD} = 3.3$ V.

2. Add an additional power consumption of 0.8 mA for the ADC and of 0.5 mA for the DAC analog part. In applications, this consumption occurs only while the ADC is on (ADON bit is set in the ADC_CR2 register).

3. An 8 MHz crystal is used as the external clock source. The AHB prescaler is used to reduce the frequency when $f_{HCLK} < 8$ MHz, the PLL is used when $f_{HCLK} > 8$ MHz.



Periph	Current consumption (µA/MHz)		
	DMA1	22.92	
AHB (up to 24MHz)	CRC	2,08	
	BusMatrix ⁽²⁾	4,17	
	APB1-Bridge	2,92	
	TIM2	18,75	
	TIM3	17,92	
	TIM4	18,33	
	TIM6	5,00	
	TIM7	5,42	
	SPI2/I2S2	4,17	
	USART2	12,08	
APB1 (up to 24MHz)	USART3	12,92	
	I2C1	10,83	
	I2C2	10,83	
	CEC	5,83	
	DAC ⁽³⁾	8,33	
	WWDG	2,50	
	PWR	2,50	
	BKP	3,33	
	IWDG	7,50	
	APB2-Bridge	3.75	
	GPIOA	6,67	
	GPIOB	6,25	
	GPIOC	7,08	
	GPIOD	6,67	
	GPIOE	6,25	
APB2 (up to 24MHz)	SPI1	4,17	
	USART1	11,67	
	TIM1	22,92	
	TIM15	14,58	
	TIM16	11,67	
	TIM17	10.83	
	ADC1 ⁽⁴⁾	15.83	

Table 18. Peripheral current consumption⁽¹⁾

1. f_{HCLK} = 24 MHz, f_{APB1} = f_{HCLK} , fAPB2 = f_{HCLK} , default prescaler value for each peripheral.

2. The BusMatrix is automatically active when at least one master is ON.

- 3. When DAC_OUT1 or DAC_OU2 is enabled a current consumption equal to 0,5 mA must be added
- Specific conditions for ADC: f_{HCLK} = 24 MHz, f_{APB1} = f_{HCLK}, f_{APB2} = f_{HCLK}, f_{ADCCLK} = f_{APB2}/2. When ADON bit in the ADC_CR2 register is set to 1, a current consumption equal to 0, 1mA must be added.



5.3.10 EMC characteristics

Susceptibility tests are performed on a sample basis during device characterization.

Functional EMS (Electromagnetic susceptibility)

While a simple application is executed on the device (toggling 2 LEDs through I/O ports). the device is stressed by two electromagnetic events until a failure occurs. The failure is indicated by the LEDs:

- Electrostatic discharge (ESD) (positive and negative) is applied to all device pins until a functional disturbance occurs. This test is compliant with the IEC 61000-4-2 standard.
- FTB: A Burst of Fast Transient voltage (positive and negative) is applied to V_{DD} and V_{SS} through a 100 pF capacitor, until a functional disturbance occurs. This test is compliant with the IEC 61000-4-4 standard.

A device reset allows normal operations to be resumed.

The test results are given in *Table 29*. They are based on the EMS levels and classes defined in application note AN1709.

Symbol	Parameter	Conditions	Level/Class
V _{FESD}	Voltage limits to be applied on any I/O pin to induce a functional disturbance	$V_{DD} = 3.3 \text{ V}, T_{A} = +25 \text{ °C},$ $f_{HCLK} = 24 \text{ MHz}, \text{ LQFP100}$ package, conforms to IEC 61000-4-2	2B
V _{EFTB}	Fast transient voltage burst limits to be applied through 100 pF on V_{DD} and V_{SS} pins to induce a functional disturbance	$V_{DD} = 3.3 \text{ V}, T_A = +25 ^{\circ}\text{C},$ $f_{HCLK} = 24 \text{ MHz}, \text{LQFP100}$ package, conforms to IEC 61000-4-4	4A

Table 29. EMS characteristics

Designing hardened software to avoid noise problems

EMC characterization and optimization are performed at component level with a typical application environment and simplified MCU software. It should be noted that good EMC performance is highly dependent on the user application and the software in particular.

Therefore it is recommended that the user applies EMC software optimization and pre qualification tests in relation with the EMC level requested for his application.

Software recommendations

The software flowchart must include the management of runaway conditions such as:

- Corrupted program counter
- Unexpected reset
- Critical Data corruption (control registers...)

Prequalification trials

Most of the common failures (unexpected reset and program counter corruption) can be reproduced by manually forcing a low state on the NRST pin or the Oscillator pins for 1 second. To complete these trials, ESD stress can be applied directly on the device, over the range of specification values. When unexpected behavior is detected, the software can be hardened to prevent unrecoverable errors occurring (see application note AN1015).



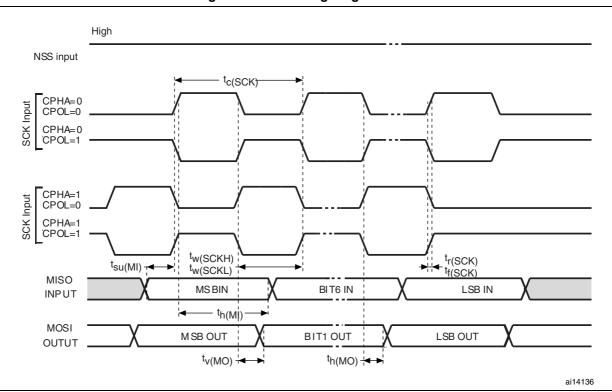


Figure 31. SPI timing diagram - master mode⁽¹⁾

1. Measurement points are done at CMOS levels: $0.3V_{DD}$ and $0.7V_{DD}$.

HDMI consumer electronics control (CEC)

Refer to *Section 5.3.12: I/O current injection characteristics* for more details on the input/output alternate function characteristics.

5.3.17 12-bit ADC characteristics

Unless otherwise specified, the parameters given in *Table 42* are derived from tests performed under the ambient temperature, f_{PCLK2} frequency and V_{DDA} supply voltage conditions summarized in *Table 8*.

Note: It is recommended to perform a calibration after each power-up.



Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
V_{DDA}	Power supply	-	2.4	-	3.6	V
V_{REF^+}	Positive reference voltage	-	2.4	-	V _{DDA}	V
I _{VREF}	Current on the V _{REF} input pin	-	-	160 ⁽¹⁾	220 ⁽¹⁾	μA
f _{ADC}	ADC clock frequency	-	0.6	-	12	MHz
f _S ⁽²⁾	Sampling rate	-	0.05	-	1	MHz
f (2)		f _{ADC} = 12 MHz	-	-	705	kHz
f _{TRIG} ⁽²⁾	External trigger frequency	-	-	-	17	1/f _{ADC}
V _{AIN} ⁽³⁾	Conversion voltage range	-	0 (V _{SSA} tied to ground)	-	V_{REF} +	V
$R_{AIN}^{(2)}$	External input impedance	See <i>Equation 1</i> and <i>Table 43</i> for details	-	-	50	κΩ
$R_{ADC}^{(2)}$	Sampling switch resistance	-	-	-	1	κΩ
C _{ADC} ⁽²⁾	Internal sample and hold capacitor	-	-	-	8	pF
• (2)	Calibratian time	f _{ADC} = 12 MHz	6.9			μs
t _{CAL} ⁽²⁾	Calibration time	-	83		1/f _{ADC}	
↓ (2)	Injection trigger conversion	f _{ADC} = 12 MHz	-	-	0.25	μs
t _{lat} (2)	latency	-	-	-	3 ⁽⁴⁾	1/f _{ADC}
t (2)	Regular trigger conversion	f _{ADC} = 12 MHz	-	-	0.166	μs
t _{latr} (2)	latency	-	-	-	2 ⁽⁴⁾	1/f _{ADC}
+ (2)	O annu lin a time a	6 40 MUL	0.125	-	20.0	μs
t _S ⁽²⁾	Sampling time	f _{ADC} = 12 MHz	1.5	-	239.5	1/f _{ADC}
t _{STAB} ⁽²⁾	Power-up time	-	0	0	1	μs
	T ()	f _{ADC} = 12 MHz	1.17	-	21	μs
t _{CONV} ⁽²⁾	Total conversion time (including sampling time)	-	14 to 252 (t _S for sa successive approx			1/f _{ADC}

Table 42. ADC characteristic	CS
------------------------------	----

1. Based on characterization results, not tested in production.

2. Guaranteed by design.

 V_{REF+} can be internally connected to V_{DDA} and V_{REF-} can be internally connected to V_{SSA}, depending on the package. Refer to *Table 4: Low & medium-density STM32F100xx pin definitions* and *Figure 6* for further details.

4. For external triggers, a delay of 1/f_{PCLK2} must be added to the latency specified in *Table 42*.

Equation 1: R_{AIN} max formula:

$$R_{AIN} < \frac{I_{S}}{f_{ADC} \times C_{ADC} \times \ln(2^{N+2})} - R_{ADC}$$

The above formula (*Equation 1*) is used to determine the maximum external impedance allowed for an error below 1/4 of LSB. Here N = 12 (from 12-bit resolution).



6 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: *www.st.com*. ECOPACK[®] is an ST trademark.

6.1 LQFP100 package information

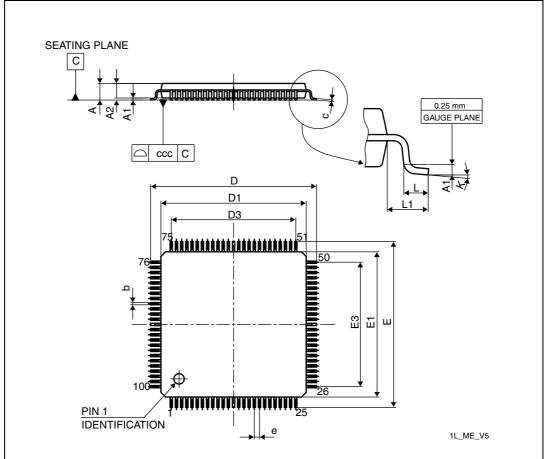


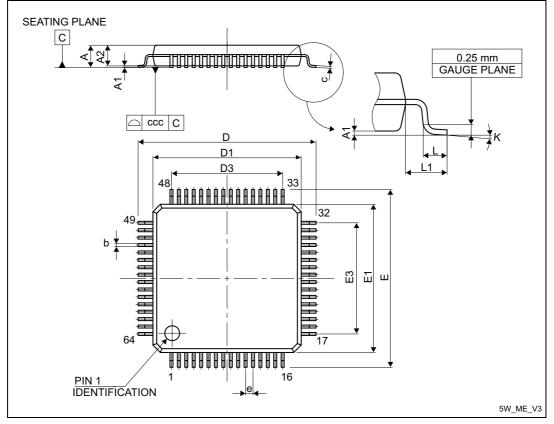
Figure 37. LQFP100 - 100-pin, 14 x 14 mm low-profile quad flat package outline

1. Drawing is not to scale. Dimensions are in millimeters.



6.2 LQFP64 package information

Figure 40.LQFP64 – 10 x 10 mm 64 pin low-profile quad flat package outline



1. Drawing is not in scale.

Table 49. LQFP64 - 64-pin, 10 x 10 mm low-profile quad flat package
mechanical data

Current e l		millimeters			inches ⁽¹⁾	
Symbol	Min	Тур	Мах	Min	Тур	Мах
А	-	-	1.600	-	-	0.0630
A1	0.050	-	0.150	0.0020	-	0.0059
A2	1.350	1.400	1.450	0.0531	0.0551	0.0571
b	0.170	0.220	0.270	0.0067	0.0087	0.0106
С	0.090	-	0.200	0.0035	-	0.0079
D	-	12.000	-	-	0.4724	-
D1	-	10.000	-	-	0.3937	-
D3	-	7.500	-	-	0.2953	-
E	-	12.000	-	-	0.4724	-
E1	-	10.000	-	-	0.3937	-
E3	-	7.500	-	-	0.2953	-



Table 50. TFBGA64 – 64-ball, 5 x 5 mm, 0.5 mm pitch, thin profile fine pitch ballgrid array package mechanical data

Symbol		millimeters	ers inche		inches ⁽¹⁾	es ⁽¹⁾	
Symbol	Min	Тур	Max	Min	Тур	Мах	
E1	-	3.500	-	-	0.1378	-	
е	-	0.500	-	-	0.0197	-	
F	-	0.750	-	-	0.0295	-	
ddd	-	-	0.080	-	-	0.0031	
eee	-	-	0.150	-	-	0.0059	
fff	-	-	0.050	-	-	0.0020	

1. Values in inches are converted from mm and rounded to 4 decimal digits.

Figure 44. TFBGA64 – 64-ball, 5 x 5 mm, 0.5 mm pitch, thin profile fine pitch ball grid array, recommended footprint

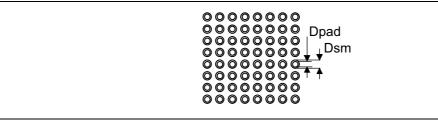


Table 51. TFBGA64 recommended PCB design rules (0.5 mm pitch BGA) Image: Comparison of the second secon

Dimension	Recommended values
Pitch	0.5
Dpad	0.280 mm
Dsm	0.370 mm typ. (depends on the soldermask registration tolerance)
Stencil opening	0.280 mm
Stencil thickness	Between 0.100 mm and 1.125 mm
Pad trace width	0.100 mm



R8_FP_V1

6.4 LQFP48 package information

SEATING PLANE A2 F 0.25 mm GAUGE PLANE ĸ D A1 D1 L1 D3 24 37 Œ b **CHE** <u>ш</u> ш Ē ----------£ 48 13 PIN 1 IDENTIFICATION 1 12 e 5B_ME_V2

Figure 46. LQFP48 - 48-pin, 7 x 7 mm low-profile quad flat package outline

1. Drawing is not to scale.

Table 52. LQFP48 - 48-pin, 7 x 7 mm low-profile quad flat package
mechanical data

		millimeters			inches ⁽¹⁾	
Symbol	Min	Тур	Мах	Min	Тур	Max
А	-	-	1.600	-	-	0.0630
A1	0.050	-	0.150	0.0020	-	0.0059
A2	1.350	1.400	1.450	0.0531	0.0551	0.0571
b	0.170	0.220	0.270	0.0067	0.0087	0.0106
С	0.090	-	0.200	0.0035	-	0.0079
D	8.800	9.000	9.200	0.3465	0.3543	0.3622
D1	6.800	7.000	7.200	0.2677	0.2756	0.2835
D3	-	5.500	-	-	0.2165	-
Е	8.800	9.000	9.200	0.3465	0.3543	0.3622



8 Revision history

Date	Revision	Changes
12-Oct-2009	1	Initial release.
26-Feb-2010	2	 TFBGA64 package added (see Table 50 and Table 41). Note 5 modified in Table 4: Low & medium-density STM32F100xx pin definitions. I_{INJ(PIN)} modified in Table 6: Current characteristics. Conditions removed from Table 25: Low-power mode wakeup timings. Notes modified in Table 34: I/O static characteristics. Figure 27: Recommended NRST pin protection modified. Note modified in Table 39: I/O static characteristics. Figure 28: I2C bus AC waveforms and measurement circuit(1) modified. Table 46: DAC characteristics modified. Figure 36: 12-bit buffered /non-buffered DAC added. TIM2, TIM3, TIM4 and TIM15, TIM16 and TIM17 updated. HDMI-CEC electrical characteristics added. Values added to: Table 12: Maximum current consumption in Run mode, code with data processing running from Flash Table 13: Maximum current consumption in Sleep mode, code running from Flash or RAM Table 14: Peripheral current consumption in Sleep mode, code running from Flash or RAM Table 15: Typical and maximum current consumptions in Stop and Standby modes Table 18: Peripheral current consumption Table 29: EMS characteristics Table 19: TS characteristics Section 5.3.12: I/O current injection characteristics modified. Added figures: Figure 12: Maximum current consumption in Run mode versus frequency (at 3.6 V) - code with data processing running from RAM, peripherals enabled Figure 13: Maximum current consumption in Run mode versus frequency (at 3.6 V) - code with data processing running from RAM, peripherals disabled Figure 15: Typical current consumption in Stop mode with regulator in Run mode versus temperature at VDD = 3.3 V and 3.6 V Figure 16: Typical current consumption in Stop mode with regulator in Run mode versus temperature at VDD = 3.3 V and 3.6 V Figure 16: Typical current consumption in Standby mode versus temperature at VDD



Date	Revision	Changes
08-Jun-2012	7	Updated Table 6: Current characteristics on page 34 Updated Table 39: I2C characteristics on page 64 Corrected note "non-robust " in Section 5.3.17: 12-bit ADC characteristics on page 68 Updated Section 5.3.13: I/O port characteristics on page 57 Updated Section 2.2.20: GPIOs (general-purpose inputs/outputs) on page 20 Updated Table 4: Low & medium-density STM32F100xx pin definitions on page 24 Updated Section 5.3.1: General operating conditions on page 34 Updated Table 14: Maximum current consumption in Sleep mode, code running from Flash or RAM on page 39
08-Jun-2015	8	Updated Table 18: Peripheral current consumption, Table 31: ESD absolute maximum ratings, Table 48: LQPF100 - 100-pin, 14 x 14 mm low-profile quad flat package mechanical data, Table 49: LQFP64 - 64- pin, 10 x 10 mm low-profile quad flat package mechanical data, Table 50: TFBGA64 – 64-ball, 5 x 5 mm, 0.5 mm pitch, thin profile fine pitch ball grid array package mechanical data, Table 51: TFBGA64 recommended PCB design rules (0.5 mm pitch BGA) and Table 52: LQFP48 - 48-pin, 7 x 7 mm low-profile quad flat package mechanical data. Updated Figure 37: LQFP100 - 100-pin, 14 x 14 mm low-profile quad flat package outline, Figure 38: LQFP100 - 100-pin, 14 x 14 mm low- profile quad flat recommended footprint, Figure 40: LQFP64 – 10 x 10 mm 64 pin low-profile quad flat package outline, Figure 41: LQFP64 - 64-pin, 10 x 10 mm low-profile quad flat recommended footprint, Figure 43: TFBGA64 – 64-ball, 5 x 5 mm, 0.5 mm pitch thin profile fine pitch ball grid array package outline, Figure 44: TFBGA64 – 64-ball, 5 x 5 mm, 0.5 mm pitch, thin profile fine pitch ball grid array, recommended footprint, Figure 46: LQFP48 - 48-pin, 7 x 7 mm low- profile quad flat package outline and Figure 47: LQFP48 - 48-pin, 7 x 7 mm low-profile quad flat package recommended footprint. Added Figure 39: LQFP100 marking example (package top view), Figure 42: LQFP64 marking example (package top view) Figure 45: TFBGA64 marking example (package top view) and Figure 48: LQFP48 marking example (package top view).
21-Nov-2016	9	Updated: – Figure 7: Memory map – Figure 18: High-speed external clock source AC timing diagram – Figure 19: Low-speed external clock source AC timing diagram – Table 19: High-speed external user clock characteristics – Table 20: Low-speed external user clock characteristics – Table 42: ADC characteristics

Table 55. Document revision history (continued)



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